

1
2
3 **UNITED STATES DISTRICT COURT**
4 **FOR THE SOUTHERN DISTRICT OF NEW YORK**

5 JAMES B. GOODMAN,

6 Plaintiff,

7 vs.

8 SAMSUNG ELECTRONICS AMERICA, INC.,
9 a New York corporation,

10 Defendant.

Civil Action No.

**COMPLAINT FOR PATENT
INFRINGEMENT AND**

DEMAND FOR JURY TRIAL

11 NOW COMES Plaintiff, JAMES B. GOODMAN (“Goodman” herein), through his
12 attorney, and files this Complaint for Patent Infringement and Demand for Jury Trial against
13 Samsung Electronics America, (“SEA” herein)

14 **PARTIES**

- 15 1. Goodman is an individual residing in the State of Texas.
- 16 2. SEA is a New York corporation with its principal place of business at 105
17 Challenger Road, Ridgefield Park, New Jersey 07660.

18 **BACKGROUND RELATING TO SEA**

- 19 3. On information and belief, SEA is a recognized innovative leader in consumer
20 electronics, mobile devices and enterprise solutions. SEA is a wholly owned
21 subsidiary of Samsung Electronics Co., Ltd. (SEC”), a Korean corporation.
- 22 4. On information and belief, products sold by SEA are sold under the trademark
23 “Samsung” to indicate that the products are connected to SEA and/or SEC.
- 24 5. According to “Samsung Newsroom U.S. (<https://news.samsung.com/us/>), SEA
25 sells cell phones such as the Galaxy S8, laptop computers such as Samsung
26 Notebook 9 Pro, Samsung desktop computers, and Chromebooks, generally under
27 the registered trademark, “Samsung”.

- 1 6. On information and belief, SEA supplies Samsung products including cell phones,
2 laptop computers, desktop computers, and Chromebooks directly and/or indirectly
3 to consumers and retail stores in this Judicial District.
- 4 7. On information and belief, many retail stores in the Judicial District work closely
5 with SEA to offer and sell Samsung products including cell phones, laptop
6 computers, desktop computers, and Chromebooks.
- 7 8. On information and belief, the retail chain “Best Buy” offers a special opportunity
8 for consumers to try, buy and learn about products from SEA in what is called,
9 “The Samsung Experience Shop” within “Best Buy” stores located in this Judicial
10 District. See <http://www.samsung.com/us/experience/skill-workshop>
- 11 9. On information and belief, SEA operates a building in New York City which SEA
12 describes as its new “flagship NYC building”, which is not a retail stores. On
13 information and belief, the building is intended to promote the Samsung brand,
14 and to provide an opportunity for consumers to try Samsung products. The
15 consumers are encouraged to purchase products online.

16 **JURISDICTION AND VENUE**

- 17 10. SEA is incorporated in the state of New York, maintains an office in this Judicial
18 District, and is using and selling in this judicial district products infringing U.S.
19 Patent No. 6,243,315 (“315 Patent”) in violation of 35 U.S.C. § 271.
- 20 11. Litigation to enforce the 315 Patent under 35 U.S.C. § 281 is proper.
- 21 12. This Court has original jurisdiction for this patent infringement case under
22 35 U.S.C. § 1338(a) and 35 U.S.C. § 1331.
- 23 13. Venue is proper in this Judicial District under 28 U.S.C. § 1391(d) and 1400(b) in
24 view of the presence and activities of SEA in this Judicial District.

25 **BACKGROUND RELATING TO GOODMAN AND HIS PATENT**

- 26 10. Goodman is the inventor and patent owner of the ‘315 Patent. The ‘315 Patent
27 leaped into importance when the manufacturers discovered the enormous
28 advantages of incorporating the claimed invention of the ‘315 Patent to reduce
power consumption and inhibit errors in devices requiring memories systems.

- 1 11. Many of the mobile phones, and computer related products sold in this Judicial
2 District by Samsung incorporate memory products known in the industry as
3 DDR3, and DDR4 memory products. Variations of these memory products such
4 as the DDR3 memory product include DDR3-800, DDR3-1066, DDR3-1333,
5 DDR3-1600, and DDR3-1666 as well as DDR3L-800, DDR3L-1066, DDR3L-
6 1333, DDR3L-1600, and DDR3L-1666. The use of the terms "DDR3", and
7 "DDR4" to include in the designation of a memory product in the industry
8 requires the performance of the memory product to comply with the respective
9 industry standards for performance, and operations.
- 10 12. The standards published by the Joint Electron Device Engineering Council Solid
11 State Technology Association ("JEDEC") state for the respective DDR3, and
12 DDR4 memory products and their variation: "No claims to be in conformance
13 with this standard may be made unless all requirements stated in the standard are
14 met."
- 15 13. On information and belief, the use of the terms "DDR3", and "DDR4", and
16 variations of each implies that the respective memory products complies with the
17 corresponding JEDEC Standards.
- 18 14. Therefore, the DDR3, and DDR4 memory products and their variations must
19 operate in compliance with the respective standards established by the JEDEC
20 Solid State Technology Association, 3103 North 10th Street, Suite 240-S,
21 Arlington, VA 22201.
- 22 15. Any memory product identified as being a DDR3 memory product, or a variation
23 thereof including the term "DDR3" must comply with JEDEC Standard
24 JESD79-3F.
- 25 16. Any memory product identified as being a DDR4 memory product, or a variation
26 thereof including the term "DDR4" must comply with JEDEC Standard
27 JESD79-4A.

1 17. On information and belief, the JEDEC Standards for DDR3, and DDR4 memory
2 products have several relevant operating capabilities in common when installed in
3 a Samsung mobile phone, or computer related product, for example: (a) Each
4 memory product has at least two banks of volatile memory, and this is the
5 equivalent of a plurality of volatile solid state memory devices under the doctrine
6 of equivalents; (b) A first external device (supplied by Samsung mobile phone,
7 and computer related product) connected to the memory product can provide
8 signals for selectively electrically isolating the address and control lines so that
9 signals on the address and control lines do not reach the memory devices; and (c)
10 A second external device (supplied by Samsung mobile phone, and computer
11 related product) connected to the memory product can determine when the
12 memory system is not being accessed and can initiate a low power for the memory
13 system wherein the first external device isolates the memory devices and places
14 the memory devices in self refresh mode, thereby reducing the electrical energy
15 drawn from the electrical power supply of the Samsung mobile phone, and
16 computer related product.

17 18. On information and belief, the aforementioned Samsung computer related
18 products incorporating a DDR3, and DDR4 provide the aforementioned first and
19 second external devices in order to take advantage of the respective operating
20 specification of the memory products, including the low power mode which saves
21 electrical energy while protecting the memory product against potential signals
22 which could damage or corrupt the stored data.

23 19. The following is a Claim Chart for Claim 1 of the '315 Patent for the DDR3
24 memory product (and similarly applies to the DDR4 memory product)
25 incorporated into a Samsung mobile phone, or computer relates systems:
26
27
28

CLAIM CHART AND ASSOCIATED CONSTRUCTION

U.S. Patent No. 6,243,315

SAMSUNG MOBILE PHONE, OR
COMPUTER RELATED SYSTEM
HAVING AN INSTALLED DDR3
MEMORY PRODUCT AND PROVIDING
THE AFOREMENTIONED FIRST AND
SECOND EXTERNAL DEVICES

Claim 1. A memory system for use in a computer system, said memory system comprising:

A “memory system” can be construed to be “a system capable of retaining data”. The JEDEC Standard JESD79-3F specification at p. 18, Sec. 3.2, “The DDR3 SDRAM is a high-speed dynamic random-access memory ...”. On the same page, “an interface designed to transfer two data words per clock cycle”. The DDR3 memory product retains data.

Thus, this memory product is within the preamble description.

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23
24
25
26
27
28

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23
24
25
26
27
28

a plurality of volatile solid state memory devices that retain information when an electrical power source is applied to said memory devices within a predetermined voltage range and

capable of being placed in a self refresh mode; said memory devices having address lines and control lines;

A “memory device” can be construed to be an **“integrated circuit or chip”**; and “a plurality of volatile solid state memory devices” can be construed to be **“two or more memory devices in the memory system into which data may be written or from which data may be retrieved that retain information while a electrical power source, having a predetermined voltage range, is applied to the memory devices and when the voltage reaches a predetermined threshold outside of that range, the memory devices will no longer retain their current state of information”**.

The JEDEC Standard JESD79-3F at p. 109, Sec. 6.1 states the absolute maximum DC Ratings. P. 111, Sec. 7.1 shows the recommended DC Operating Conditions with a minimum and maximum for the DC voltages.

The JEDEC Standard JESD79-3F in at p. 77 refers to the memory module as being a “chip”. See Sec. 4.15.

The JEDEC Standard JESD79-3F at p. 18, Sec. 3.2 states, “The DDR3 SDRAM is a high-speed dynamic random-access internally configured a an eight-bank DRAM.” The second paragraph describes how a bank can be selected. See the Command Truth Table at p. 33, Sec. 4.1, and NOTE 3 explains that “BA” is for the selection of a bank being operated upon. Hence, the DDR3 has eight memory banks and the equivalents of a plurality of solid state memory devices.

On information and belief, a DRAM is volatile memory and that means a voltage in a specific range must be applied to operate acceptably as pointed out above.

The JEDEC Standard JESD79-3F shows that the DDR3 is capable of being refreshed at p. 13, Sec. 2.10 for CKE, (CKE0), (CKE1) “Self-Refresh operations (all banks idle)”; p. 17, Sec. 3.1 on the diagram; p. 31, Sec. 3.4.4.1 entitled “Partial Array Self-Refresh (PASR)”; p. 35, Sec. 4.2 shows an entry for “Self-Refresh”; p. 46, Sec. 4.9.0.1 entitled, “Auto Self-Refresh”; and p. 79, Sec. 4.16 entitled “Self-Refresh Operation”.

1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23
24
25
26
27
28

a control device for selectively electrically isolating said memory devices from respective address lines and respective control lines so that when said memory devices are electrically isolated, any signals received on said respective address lines and respective control lines do not reach said memory devices; and

a memory access enable control device coupled to said control device and to said control lines for determining when said memory system is not being accessed and for initiating a low power mode for said memory system wherein said control device electrically isolates said memory devices and places said memory devices in said self refresh mode, thereby reducing the amount of electrical energy being drawn from an electrical power supply for said computer system.

JEDEC Standard JESD79-3F at p. 81, Sec. 4.17.1 entitled "Power-Down Entry and Exit" discloses a power-down operation. The description states, "Entering power-down deactivates the input and output buffers, excluding CK, CK#, ODT, CKE, and RESET#. To protect DRAM internal delay on CKE line to block the input signals, multiple NOP or Deselect commands are needed during the CKE switch off and cycle(s) after, this timing period are defined as tCPDED. CKE_low will result in deactivation of command and receivers after tCPDED has expired. The text also states, "In power-down mode, CKE low, RESET# high, and stable clock signal must be maintained at the inputs of the DDR3 SDRAM, and ODT should be in a valid state, but all other input signals are "Don't Care." The input signals are address and control signals are related to the CK# input noted at p. 13, Sec. 2.10, where it is stated, "All Address and control input signals are sampled on the crossing of the positive edge of CK and negative edge of CK#.

The power-down is due to an input signal from the second external device as pointed out at P. 13, Sec. 2.10. The device generating the input signal for the power-down functions like the claimed memory access enable control device. JEDEC Standard JESD79-3F , Sec. 4.17.1 states, " Power-down is synchronously entered when CKE is registered low (along with NOP or Deselect command). CKE is not allowed to go low while mode register set command, MPR operations, ZQCAL operations, DLL locking or read/write operations are in progress.

JURY DEMAND

Pursuant to Fed. R. Civ. P. 38(b), Plaintiff hereby demands a jury trial as to all issues in this lawsuit.

PRAYER FOR RELIEF

THEREFORE, Plaintiff respectfully requests this Court to:

- a. enter judgment for Plaintiff on Claim 1 of the '315 Patent for patent infringement, either literally, and/or under the doctrine of equivalents against SEA;
- b. order that an accounting be had for the damages caused to the Plaintiff by the infringing activities of the SEA;
- c. enter an injunction to prohibit SEA from directly or indirectly from offering for sale, or selling infringing products;
- d. award Plaintiff interest and costs from SEA;
- e. find SEA liable for willful infringement;
- f. award Plaintiff enhanced damages due to willful infringement by SEA; and
- e. award Plaintiff such other and further relief as this Court may deem just and equitable.

THE PLAINTIFF

JAMES B. GOODMAN

Date: July 20, 2017

/s/ David Fink
 David Fink
 Reg. No. 299869
 Fink & Johnson
 7519 Apache Plume
 Houston, Texas 77071
 713.729.4991 Tel.; 713.729.8408 Fax
 Attorney in Charge for the Plaintiff